

High Power LED chip 2500 A.

High Power
N UV.

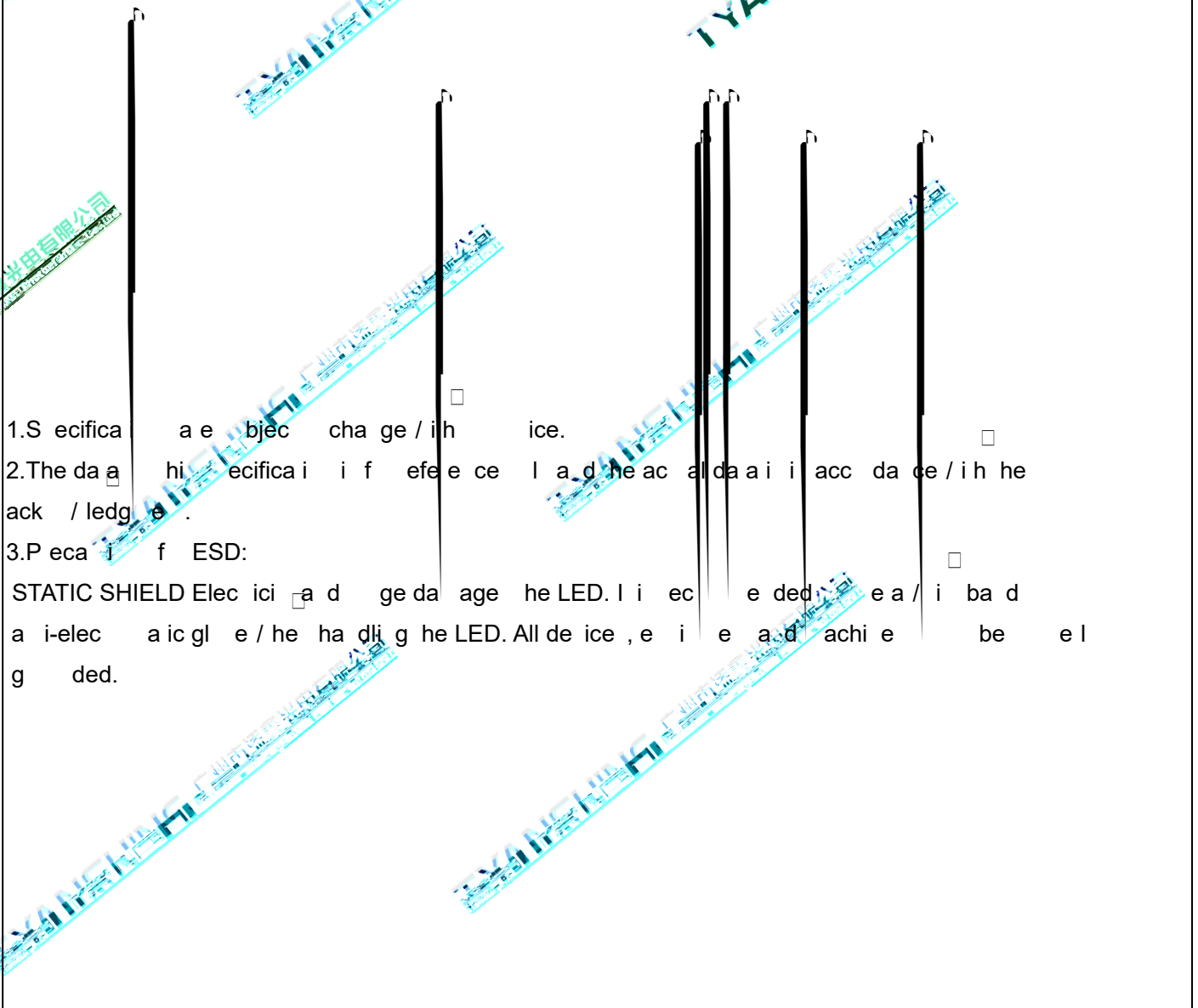
High Power LED chip 2500 A.

GaN

GaN

High Power LED chip
High Power LED chip
High Power LED chip

F / adC e	IF	2500	A
Re e eV l age	V _R	N de ig ed f e e e e a i	V
P / e Di i ai	P _D	9.5	W
J ci Te e a e	T _j	150	
Elec a ic Di cha ge Th e h ld (ESD)	ESD	ESD e ii e de ice	V
S age Te e a e	T _g	-40 +70	
O e ai Te e a e	T	-80 +85	



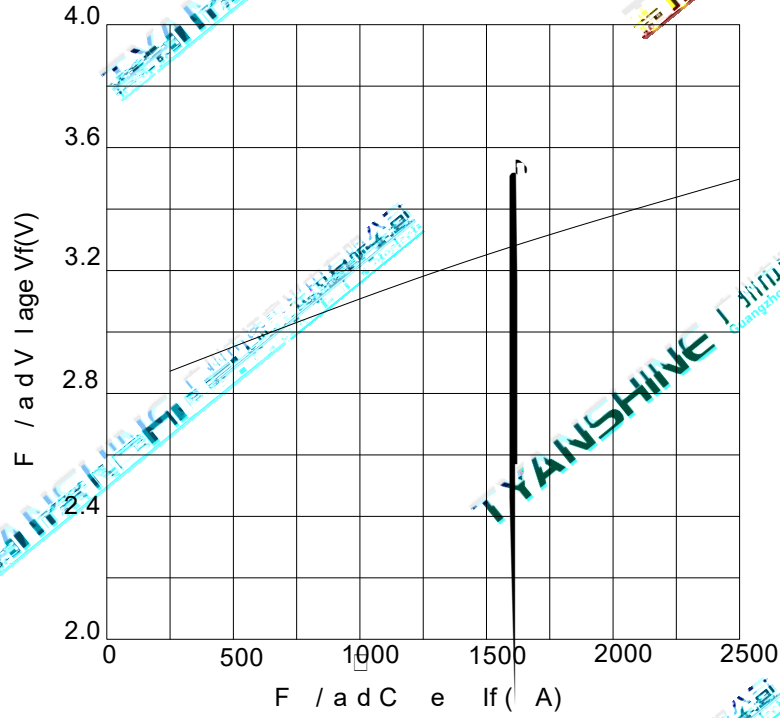
1. Specific a e bjec cha ge / i h ice.
2. The da a hi e cifica i i f efe e ce l a d he ac al da a i i acc da ce / i h he ack / ledg e .
3. P eca i f ESD:
 STATIC SHIELD Elec ici a d ge da age he LED. l i ec e ded e a / i ba d a i-elec a ic gl e / he ha dli g he LED. All de ice , e i e a d achi e be e l g ded.

L i F l			270	300	330		l
F / a d V l a g e	V_f		2.8	3.1	3.4		V
Vie/ i g A g l e a 50 IV	$2^{1/2}$	If=1000 A		120			Deg
Peak E i i W a e l e g h			518	523	528		
D i a W a e l e g h	d		525	530	535		
Vie/ i g A g l e a 50 IV	$2^{1/2}$		28	33	38		
Re e e C e	I_R						A
The al Re i a c e J c i C a e	R_{j-c}	If=1000 A		4.9			K/W
Te e a e C e f f i c i e f V l a g e	V F/T			-2			V/

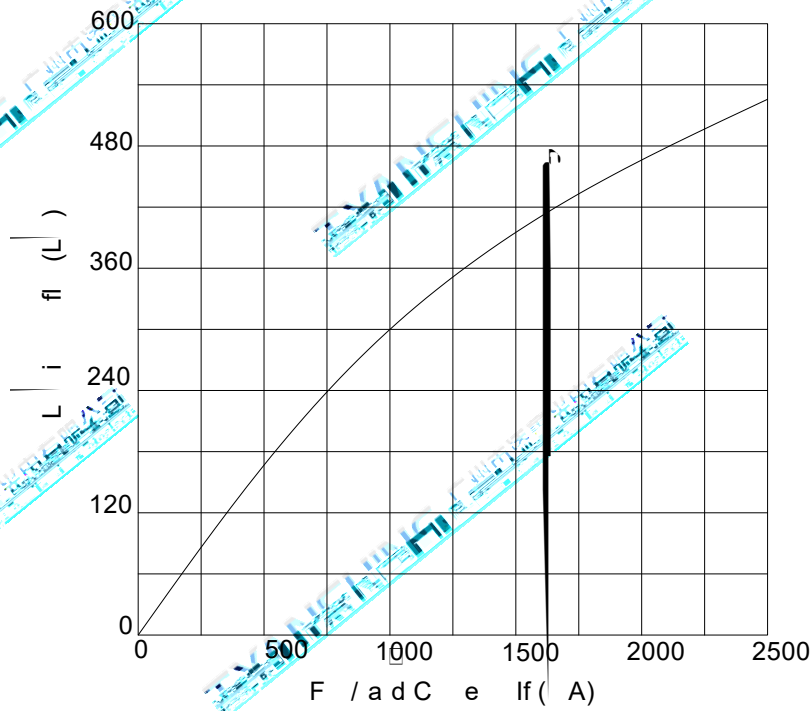
1. L i i e i i e a e d / i h a l i g h e a d f i l e c b i a i h a a i a e h e C I E e e e e c e .
2. $1/2$ i h e f f a i a g l e a / h i c h h e l i i e i i h a l f h e a i a l i i e i .
3. L i □ f l e a e e l e a c e : 15% .
4. F / a d l a g e e a e e l e a c e : 10% V .

(25 A bie Te ea eU le Ohe / i eN ed)

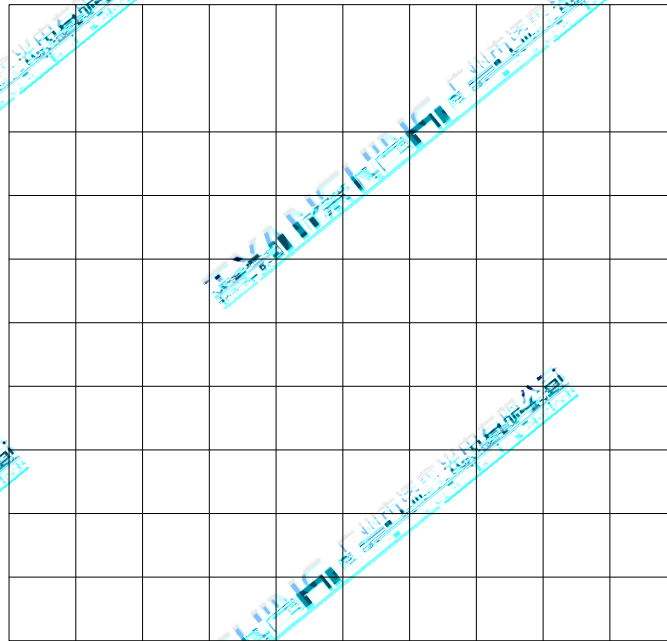
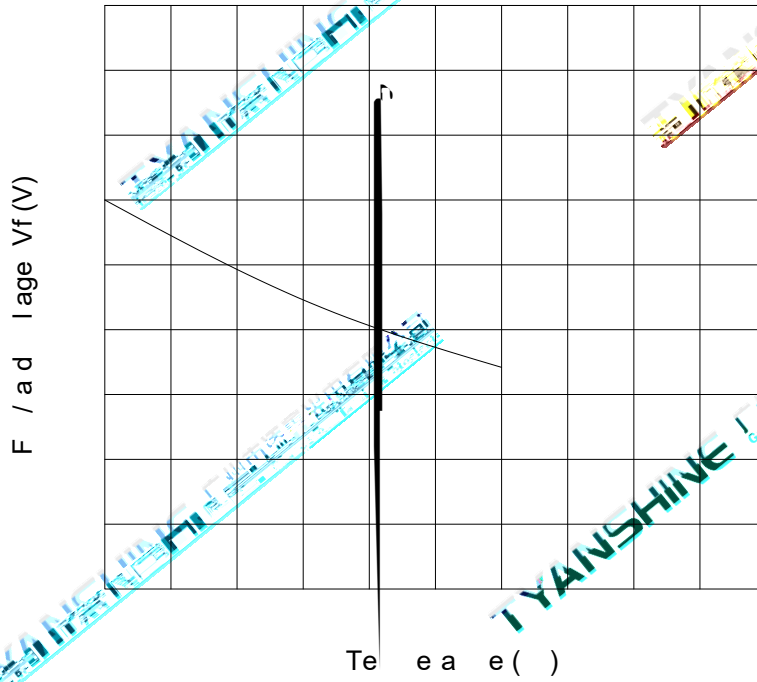
F / a d C e VS. F / a d V l a g e

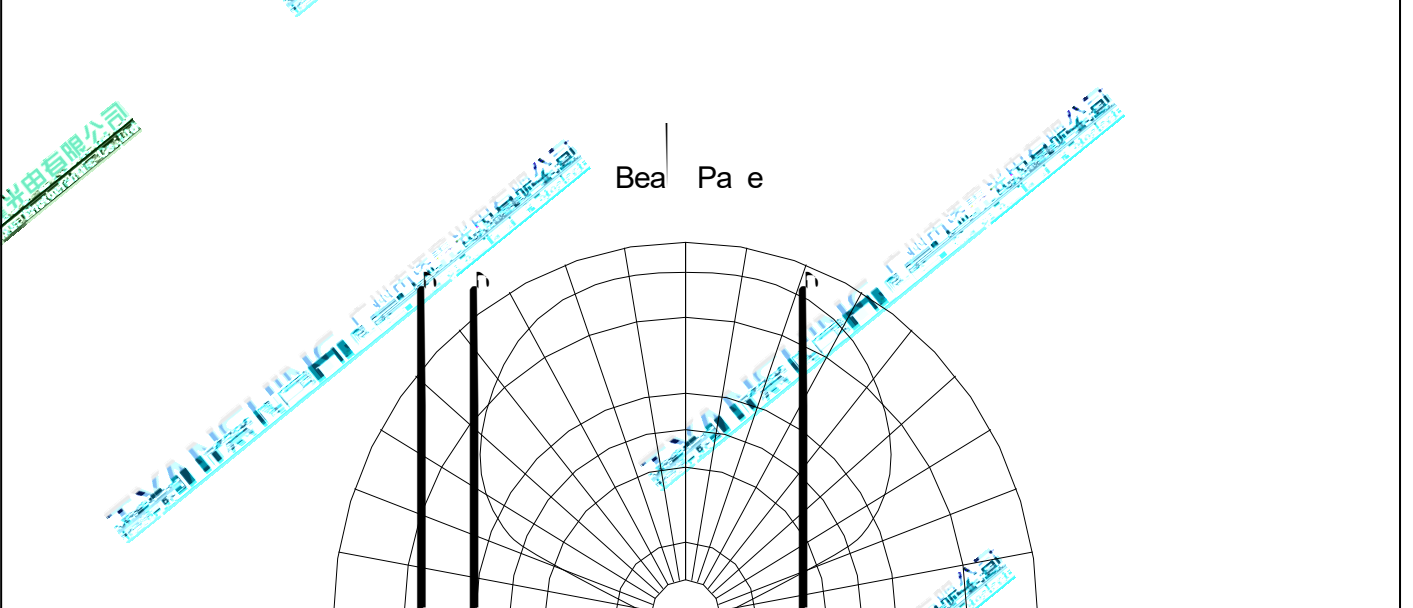
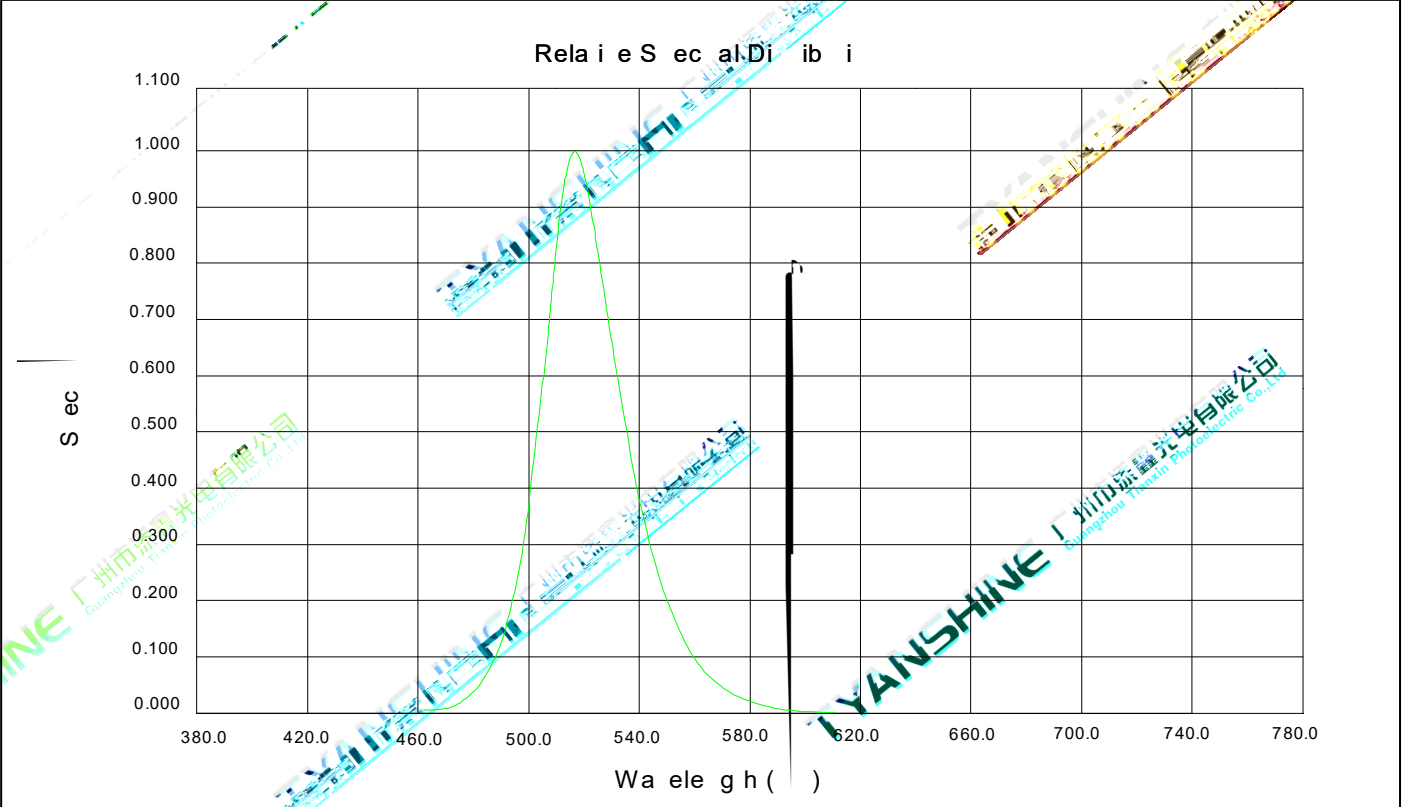


F / a d C e VS. L i f l



Temperature VS. Forward Voltage (IF=1000 A)





Relative Intensity (LOP@MAX=1)

1. 2 1/2 degree half angle beam diameter / half angle beam diameter = 1/2 beam diameter.

2. View angle less than 5 degrees.

Temperature: 5 30 (41 86)

Humidity: 60% RH Max.

Use the circuit in the figure.

